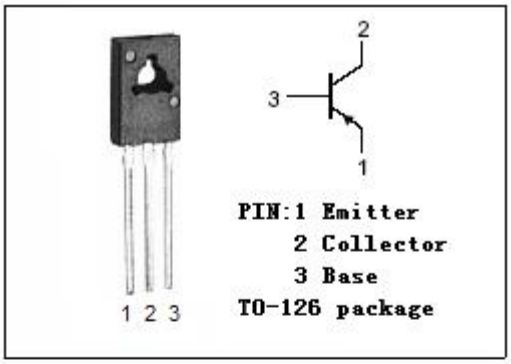
isc Silicon PNP Power Transistor 2SB549

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -100V(Min)
- With TO-126 package
- Complement to Type 2SD415
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

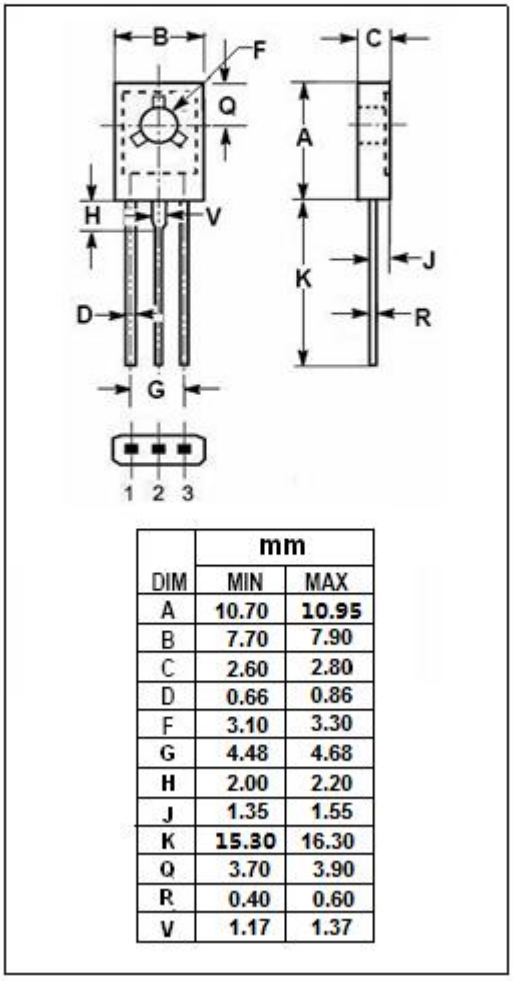


APPLICATIONS

- Designed for low frequency power amplifiers applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-0.8	A
I_{CM}	Collector Current-Peak	-1.5	A
P_C	Collector Power Dissipation @Ta=25℃	1	W
	Collector Power Dissipation @T_C=25℃	10	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

Powisc Silicon PNP er Transistor 2SB549

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA; R_{BE}=∞	-100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -80V; I_E= 0			-1	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -3V; I_C= 0			-1	μA
h_{FE-1}	DC Current Gain	I_C= -2mA; V_{CE}= -5V	20			
h_{FE-2}	DC Current Gain	I_C= -0.2A; V_{CE}= -5V	40		320	
C_{OB}	Output Capacitance	I_E=0; V_{CB}= -10V; f= 1MHz		25		pF
f_T	Current-Gain—Bandwidth Product	I_C=-0.1A ; V_{CE}= -5V		70		MHz

◆ **h_{FE-2}Classifications**

S	R	Q	P
40-80	60-120	100-200	160-320